

SMMBTA56LT1G Datasheet



SMMBTA56LT1G-DG
onsemi
SMMBTA56LT1G
TRANS PNP 80V 0.5A SOT23-3
Bipolar (BJT) Transistor PNP 80 V 500 mA 50MHz 22 5 mW Surface Mount SOT-23-3 (TO-236)

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SMMBTA56LT1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
80 V	250mV @ 10mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100nA	100 @ 100mA, 1V
Power - Max:	Frequency - Transition:
225 mW	50MHz
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SOT-23-3 (TO-236)
Base Product Number:	
SMMBTA56	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

8541.21.0095

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Driver Transistors

PNP Silicon

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBTA55 MMBTA56, SMMBTA56	V _{CEO}	-60 -80	Vdc
Collector – Base Voltage MMBTA55 MMBTA56, SMMBTA56	V _{CBO}	-60 -80	Vdc
Emitter-Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current – Continuous	Ι _C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

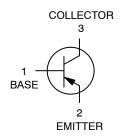
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

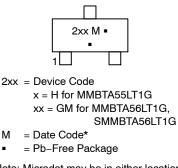
2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.



SOT-23 CASE 318 STYLE 6



MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				-
	V _(BR) CEO	-60 -80		Vdc
Emitter – Base Breakdown Voltage ($I_E = -100 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	-4.0	_	Vdc
Collector Cutoff Current ($V_{CE} = -60 \text{ Vdc}, I_B = 0$)	I _{CES}	_	-0.1	μAdc
	I _{CBO}	-	-0.1 -0.1	μAdc
ON CHARACTERISTICS				

DC Current Gain ($I_C = -10 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -100 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$)	h _{FE}	100 100		-
Collector – Emitter Saturation Voltage $(I_C = -100 \text{ mAdc}, I_B = -10 \text{ mAdc})$	V _{CE(sat)}	-	-0.25	Vdc
Base – Emitter On Voltage (I _C = –100 mAdc, V _{CE} = –1.0 Vdc)	V _{BE(on)}	_	-1.2	Vdc

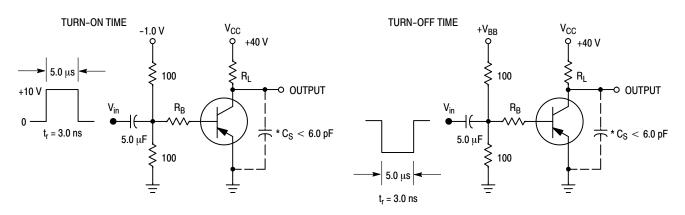
SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (Note 4)	f _T			MHz
(I _C = -100 mAdc, V _{CE} = -1.0 Vdc, f = 100 MHz)		50	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

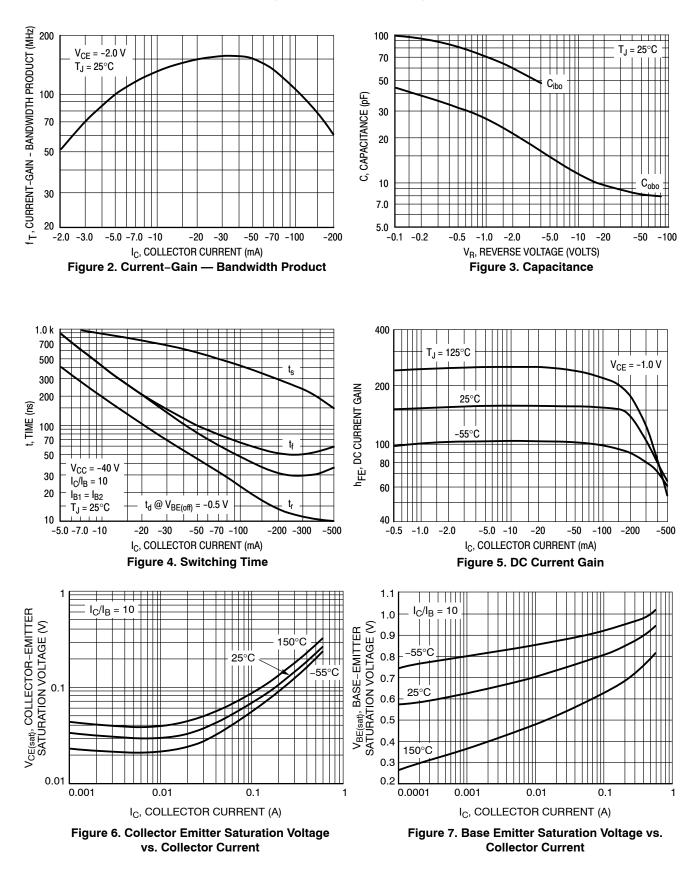
4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



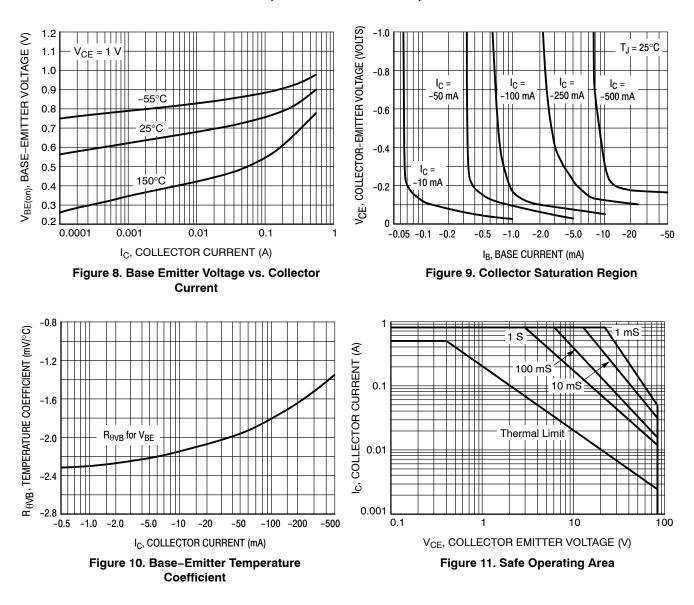
*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series



MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series



ORDERING INFORMATION

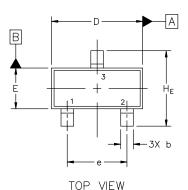
Device Order Number	Package Type	Shipping [†]
MMBTA55LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA55LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

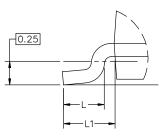
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

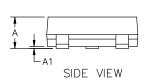
PACKAGE DIMENSIONS

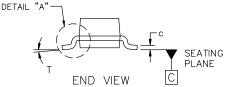
SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

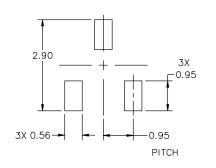




DETAIL "A" Scale 3:1







MILLIMETERS				
DIM	MIN	NOM	MAX	
A	0.89	1.00	1.11	
A1	0.01	0.06	0.10	
b	0.37	0.44	0.50	
с	0.08	0.14	0.20	
D	2.80	2.90	3.04	
E	1.20	1.30	1.40	
е	1.78	1.90	2.04	
L	0.30	0.43	0.55	
L1	0.35	0.54	0.69	
He	2.10	2.40	2.64	
Т	0°		10°	

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- 2.
- MILLIMETERS MAXIMUM LEAD THICKNESS
- 3 INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4 PROTRUSIONS, OR GATE BURRS.

STYLE 6: PIN 1. BASE 2 EMITTER COLLECTOR 3

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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